MANUFACTURE OF SEMICONDUCTOR DEVICE, MANUFACTURE OF ELECTRO-OPTICAL DEVICE, SEMICONDUCTOR DEVICE AND THE ELECTRO-OPTICAL DEVICE

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Abstract of **JP2000312006**

PROBLEM TO BE SOLVED: To provide a highly reliable semiconductor device or an electro-optical device having a thin-film transistor, and having no alignment deviation, even when the thin film transistor is brought into a microscopic state. SOLUTION: A liquid crystal device, which is an example of an electro-optical device, is provided with a TFT 30 formed on a TFT array substrate 10, a data line 6a, a scanning line 3a, the second capacitor electrode 3b and a pixel electrode 9a. The pixel electrode and the TFT are electrically connected by two contact holes 8a and 8b relayed by a conductive layer 80a. A second insulating thin film 81 is pinched by the second capacity electrode and a part of the conductive layer, and the second accumulation capacitor is formed. The second insulating thin film is composed of the scanning line and the oxide film of the second capacitor electrode.